NSN 5961-01-525-8945

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Overall Length:

Between 33.9 millimeters and 35.1 millimeters

Overall Width:

Between 15.3 millimeters and 15.9 millimeters

End Application:

Power unit, 0.8 kw, dc, 841-01.

Mounting Facility Quantity:

3

Mounting Method:

Slot and slot and threaded hole

Voltage Rating In Volts Per Characteristic:

600.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter and 18.0 breakdown voltage, emitter to collector, base open

Power Rating Per Characteristic:

160.0 watts small-signal input power, common-collector absolute

Special Features:

Vshort circuit rated ultrafast: optimized for high operating frequencies >5.0 khz, and short circuit rated to 10 us @ 125 deg. Celsius, vge= 15 v. Industry standard t0-247ac package. Generation 4 insulated gate bipolar transistor.

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0